

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
07 September 2023 (07.09.2023)



(10) International Publication Number
WO 2023/167864 A1

(51) International Patent Classification:

H03F 1/14 (2006.01) H03F 3/45 (2006.01)
H03F 3/193 (2006.01) H03F 1/56 (2006.01)
H03F 3/24 (2006.01)

(21) International Application Number:

PCT/US2023/014135

(22) International Filing Date:

28 February 2023 (28.02.2023)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

17/683,607 01 March 2022 (01.03.2022) US
17/945,520 15 September 2022 (15.09.2022) US

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS,

(54) Title: AMPLIFIER WITH PARASITIC CAPACITANCE NEUTRALIZATION

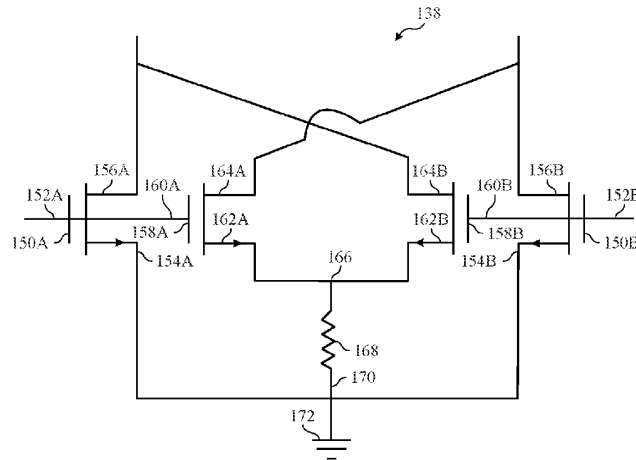


FIG. 8

(57) Abstract: Amplification circuitry is disclosed that couples neutralization transistors to amplification transistors to neutralize parasitic capacitance of the amplification transistors. Gates of a first amplification transistor and a first neutralization transistor are coupled together, and gates of a second amplification transistor and a second neutralization transistor are also coupled together. Drains of the first amplification transistor and the second neutralization transistor are coupled together, and drains of the second amplification transistor and the first neutralization transistor are also coupled together. Sources of neutralization transistors are coupled together at a node, such that a voltage swing of a first signal in the first neutralization transistor may be canceled by a voltage swing of a second signal in the second neutralization transistor. The node also couples to a resistor that prevents charge building in the neutralization transistors.

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RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH,
TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS,
ZA, ZM, ZW.

- (84) Designated States** (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

- *as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))*
- *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))*

Published:

- *with international search report (Art. 21(3))*
- *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))*